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Kind regards,

Team Nexperia



# PESD1FLEX

# FlexRay bus ESD protection diode Rev. 02 — 15 February 2008

**Product data sheet** 

### **Product profile**

### 1.1 General description

PESD1FLEX in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package designed to protect two automotive FlexRay bus lines from the damage caused by ElectroStatic Discharge (ESD) and other transients.

#### 1.2 Features

- Due to the integrated diode structure only one small SOT23 package is needed to protect two FlexRay bus lines
- Max. peak pulse power:  $P_{PP} = 200 \text{ W}$  at  $t_p = 8/20 \text{ μs}$
- Low clamping voltage: V<sub>CL</sub> = 40 V at I<sub>PP</sub> = 1 A
- Ultra low leakage current: I<sub>RM</sub> < 1 nA</p>
- Typ. diode capacitance matching:  $\Delta C_d/C_d = 0.1 \%$
- ESD protection up to 23 kV
- IEC 61000-4-2, level 4 (ESD)
- IEC 61000-4-5 (surge);  $I_{PP} = 3$  A at  $t_p = 8/20$  μs
- Small SMD plastic package

### 1.3 Applications

- FlexRay bus protection
- Automotive applications

### 1.4 Quick reference data

Table 1. Quick reference data

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	)					
$V_{RWM}$	reverse standoff voltage		-	-	24	V
C <sub>d</sub>	diode capacitance	$f = 5 \text{ MHz}; V_R = 0 \text{ V}$	-	11	17	pF



# 2. Pinning information

Table 2. Pinning

	3		
Pin	Description	Simplified outline	Symbol
1	cathode 1		
2	cathode 2	<u>    3</u>	1   [C D]
3	common cathode	1 2	2 3
			006aaa155

# 3. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
PESD1FLEX	-	plastic surface-mounted package; 3 leads	SOT23			

# 4. Marking

Table 4. Marking codes

Type number	Marking code <sup>[1]</sup>
PESD1FLEX	ZJ*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
P <sub>PP</sub>	peak pulse power	$t_p = 8/20 \; \mu s$	[1][2]	200	W
I <sub>PP</sub>	peak pulse current	$t_p = 8/20 \; \mu s$	[1][2]	3	Α
Per device					
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		<b>–65</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Non-repetitive current pulse 8/20  $\mu s$  exponential decay waveform according to IEC 61000-4-5.
- [2] Measured from pin 1 to 3 or 2 to 3.

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Table 6. ESD maximum ratings

Symbol	Parameter	Conditions		Min	Max	Unit
Per diode						
V <sub>ESD</sub>	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	[1][2]	-	23	kV
		MIL-STD-883 (human body model)		-	10	kV

- [1] Device stressed with ten non-repetitive ESD pulses.
- [2] Measured from pin 1 to 3 or 2 to 3.

Table 7. ESD standards compliance

Standard	Conditions
Per diode	
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3 (human body model)	> 4 kV

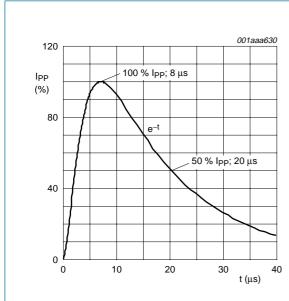


Fig 1. 8/20  $\mu s$  pulse waveform according to IEC 61000-4-5

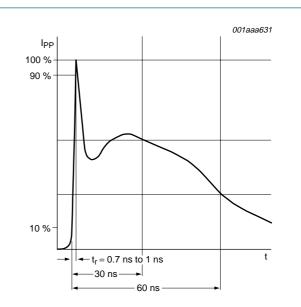


Fig 2. ESD pulse waveform according to IEC 61000-4-2

### 6. Characteristics

Table 8. Characteristics

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{RWM}$	reverse standoff voltage		-	-	24	V
I <sub>RM</sub>	reverse leakage current	V <sub>RWM</sub> = 24 V	-	< 1	50	nΑ
$V_{BR}$	breakdown voltage	$I_R = 5 \text{ mA}$	25.4	27.8	30.3	V
C <sub>d</sub>	diode capacitance	$f = 5 \text{ MHz}; V_R = 0 \text{ V}$	-	11	17	pF
$\Delta C_d/C_d$	diode capacitance matching		<u>[1]</u>			
		$f = 5 \text{ MHz}; V_R = 0 \text{ V}$	-	0.1	-	%
		f = 5 MHz; V <sub>R</sub> = 2.5 V	-	0.1	-	%
$V_{CL}$	clamping voltage		[2][3]			
		I <sub>PP</sub> = 1 A	-	-	40	V
		I <sub>PP</sub> = 3 A	-	-	70	V
r <sub>dif</sub>	differential resistance	I <sub>R</sub> = 1 mA	-	-	300	Ω

<sup>[1]</sup>  $\Delta C_d$  is the difference of the capacitance measured between pin 1 and pin 3 and the capacitance measured between pin 2 and pin 3.

<sup>[2]</sup> Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

<sup>[3]</sup> Measured from pin 1 to 3 or 2 to 3.

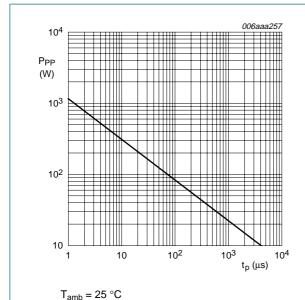


Fig 3. Peak pulse power as a function of exponential pulse duration; typical values

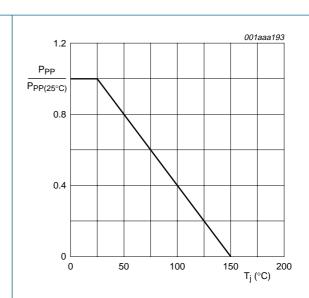


Fig 4. Relative variation of peak pulse power as a function of junction temperature; typical values

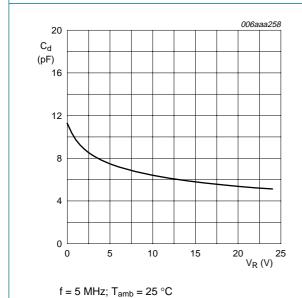


Fig 5. Diode capacitance as a function of reverse voltage; typical values

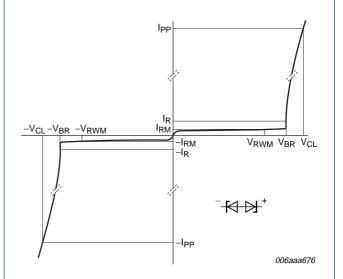
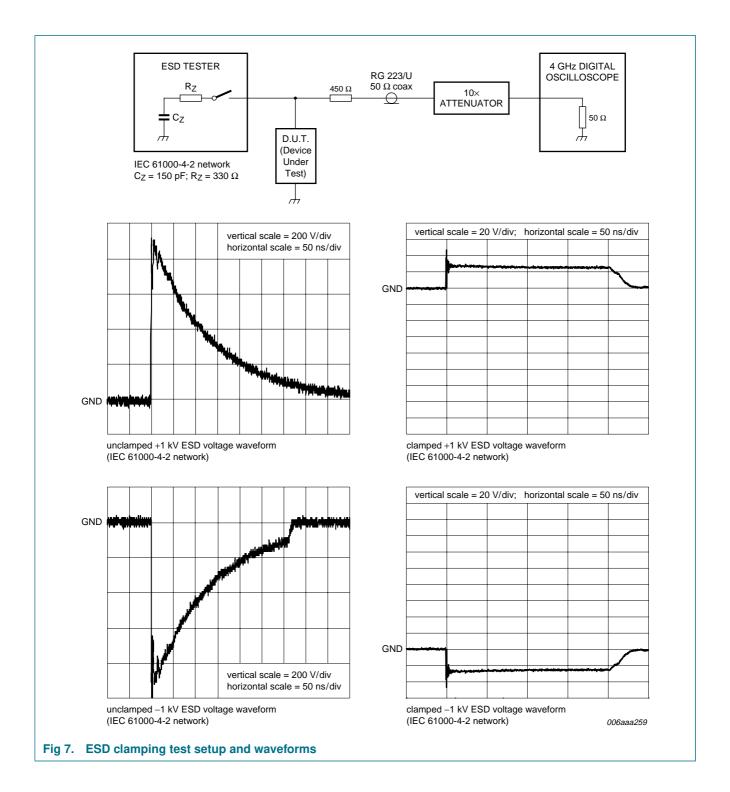


Fig 6. V-I characteristics for a bidirectional ESD protection diode

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**Product data sheet** 





**Product data sheet** 

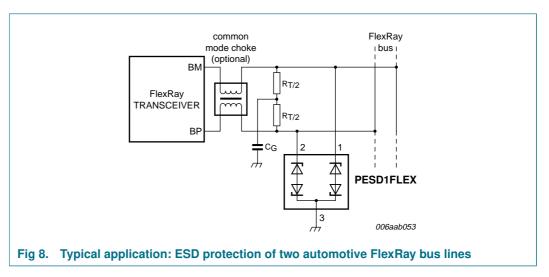
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FlexRay bus ESD protection diode

#### **Application information** 7.

The PESD1FLEX is designed for the protection of two automotive FlexRay data lines from the damage caused by ESD and surge pulses. The device supports a FlexRay data rate of 10 Mbit/s. The PESD1FLEX provides a surge capability of up to 200 W per line for an 8/20 μs waveform.

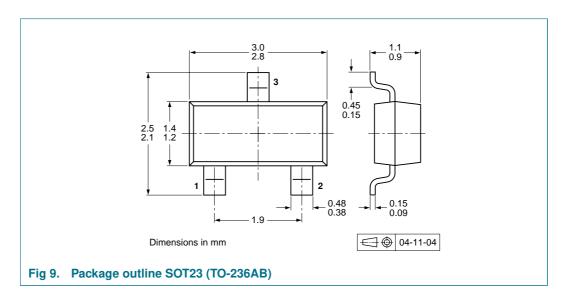


#### Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the PESD1FLEX as close to the input terminal or connector as possible.
- 2. The path length between the PESD1FLEX and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protection conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

# 8. Package outline



# 9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

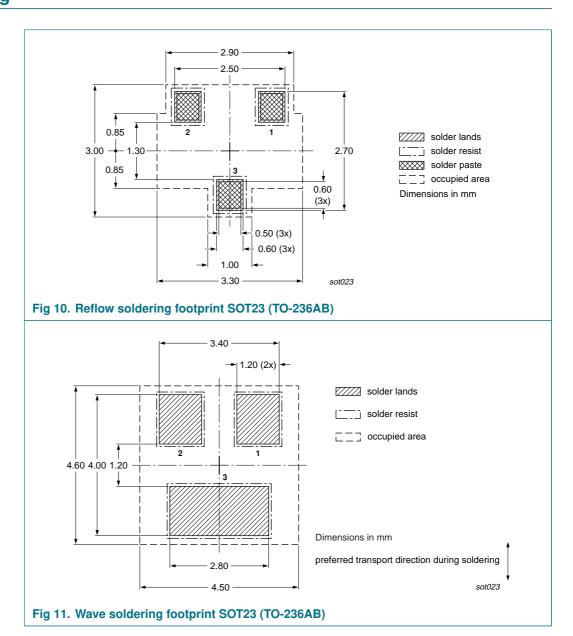
Type number	Package	Description	Packing quantity	
			3000	10000
PESD1FLEX	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235

[1] For further information and the availability of packing methods, see Section 13.

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### FlexRay bus ESD protection diode

# 10. Soldering



**Product data sheet** 



# 11. Revision history

### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
PESD1FLEX_2	20080215	Product data sheet	-	PESD1FLEX_1		
Modifications:	Section 1.2 "Features": list item for diode capacitance matching added					
	• Table 8 "Cha	$\frac{1}{2}$ $\Delta C_d/C_d$ diode ca	pacitance matching	added		
PESD1FLEX_1	20070521	Product data sheet	-	-		

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### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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# **PESD1FLEX**

### FlexRay bus ESD protection diode

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